

**High-Frequency SPDT Antenna Switch**

**Description**

The CXG1006N is a high power antenna switch MMIC. This IC is designed using the Sony's GaAs J-FET process and operates at a single positive power supply.

**Features**

- Single positive power supply operation
- Low insertion loss 0.5dB (Typ.) at 2.0GHz
- High isolation 27dB (Typ.) at 2.0GHz
- High power switching
 

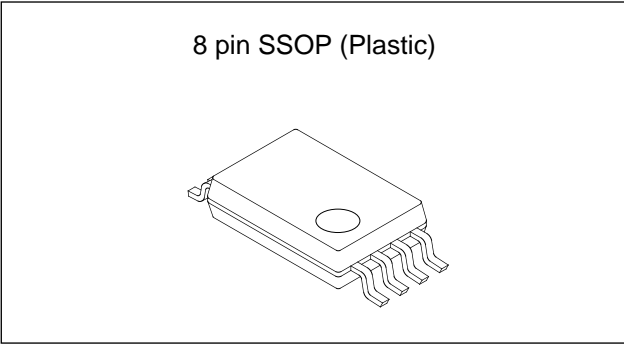
P1dB (Typ.)	32dBm	at 2.0GHz	$V_{CTL} (H) = 2.0V$
	34dBm	at 2.0GHz	$V_{CTL} (H) = 4.0V$

**Application**

Antenna switch for digital cellular telephones

**Structure**

GaAs J-FET MMIC



**Absolute Maximum Ratings (Ta = 25°C)**

- Control voltage  $V_{ctl}$  7 V
- Operating temperature  $T_{opr}$  -35 to +85 °C
- Storage temperature  $T_{stg}$  -65 to +150 °C

**Operating Condition**

Control voltage 0/4 V

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**Electrical Characteristics**

**V<sub>CTL (L)</sub> = 0V, V<sub>CTL (H)</sub> = 4V, P<sub>IN</sub> = 30dBm, R<sub>RF</sub> = 75kΩ** (Ta = 25°C)

Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Insertion Loss	IL1	f = 1.0GHz	35	0.3	0.6	dB
Isolation	ISO1			40		
Insertion Loss	IL1.5	f = 1.5GHz	29	0.4	0.7	dB
Isolation	ISO1.5			32		
Insertion Loss	IL2	f = 2.0GHz	24	0.5	0.8	dB
Isolation	ISO2			27		
VSWR	VSWR				1.5	
Switching Time	TSW				100	

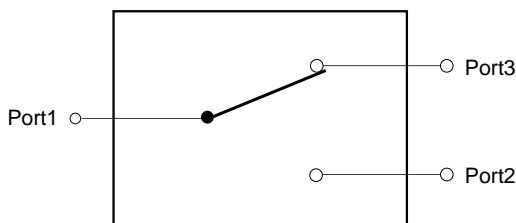
**V<sub>CTL (L)</sub> = 0V, f = 2GHz** (Ta = 25°C)

Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
1dB Compression Point	P1dB (3)	V <sub>CTL (H)</sub> = 3V	30	32		dBm
1dB Compression Point	P1dB (4)	V <sub>CTL (H)</sub> = 4V	32	34		dBm

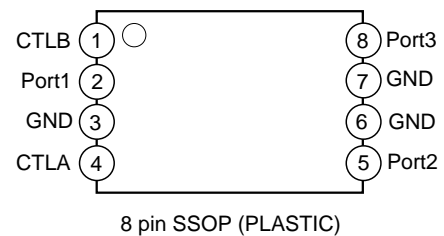
**V<sub>CTL (L)</sub> = 0V, R<sub>RF</sub> = 75kΩ** (Ta = 25°C)

Item	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Control Current	I <sub>CTL (1)</sub>	V <sub>CTL (H)</sub> = 3V		100	170	μA
Control Current	I <sub>CTL (2)</sub>	V <sub>CTL (H)</sub> = 4V		150	220	μA
Control Current	I <sub>CTL (3)</sub>	V <sub>CTL (H)</sub> = 5V		200	270	μA

**Block Diagram**



**Package Outline/Pin Configuration**



V <sub>CTLA</sub>	V <sub>CTLB</sub>	
High	Low	Port1-Port2 ON Port1-Port3 OFF
Low	High	Port1-Port2 OFF Port1-Port3 ON

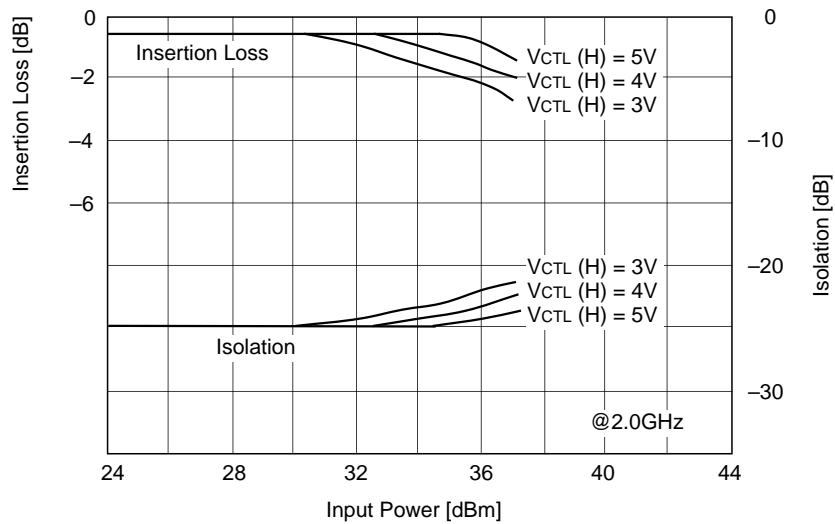
Recommended Circuit



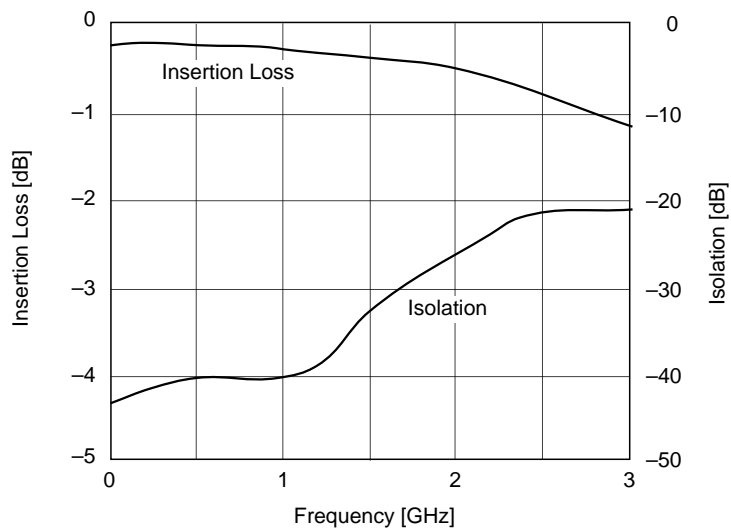
\* RRF is used to stabilize the electrical characteristics at high power signal input

Example of Representative Characteristics (Ta = 25°C)

Insertion Loss and Isolation vs. Input Power



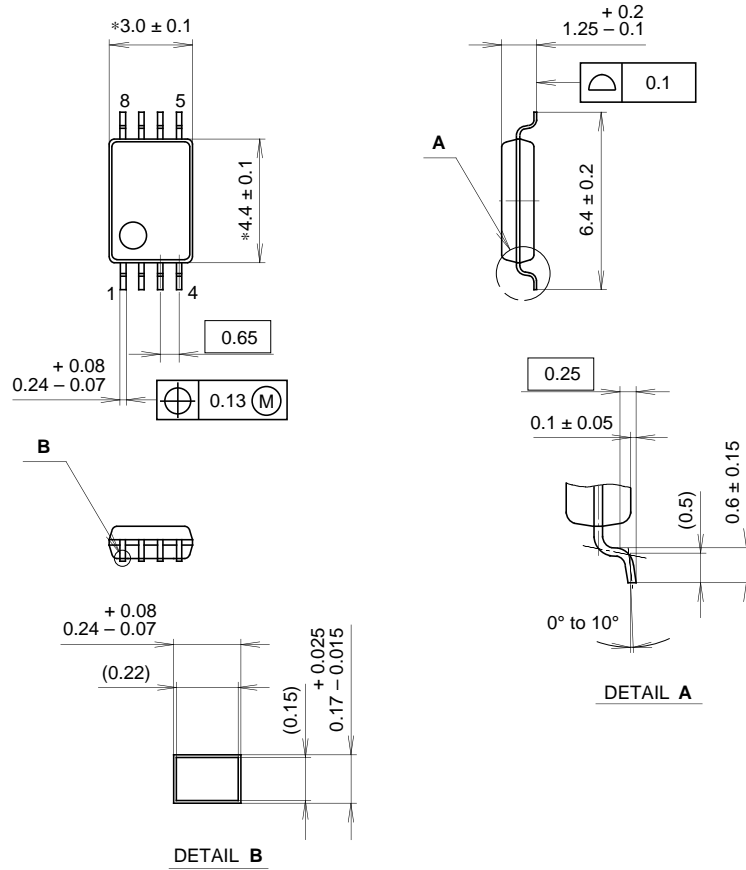
Insertion Loss and Isolation vs. Frequency



Package Outline

Unit: mm

8PIN SSOP (PLASTIC)



NOTE: Dimension "\*" does not include mold protrusion.

PACKAGE STRUCTURE

SONY CODE	SSOP-8P-L01
EIAJ CODE	SSOP008-P-0044
JEDEC CODE	

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	SOLDER / PALLADIUM PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE WEIGHT	0.04g